Product data sheet

1. General description

NPN low V_{CEsat} transistor in a medium power flat lead SOT89 plastic package.

PNP complement: PBSS5320X

2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements.
- AEC-Q101 qualified

3. Applications

- Power management
 - · DC/DC converters
 - · Supply line switching
 - · Battery charger
 - LCD backlighting.
- Peripheral drivers
 - · Driver in low supply voltage applications (e.g. lamps and LEDs).
 - · Inductive load driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	20	V
I _C	collector current		[1]	-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	5	Α
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 0.1 \text{ A}$		220	-	-	
R _{CEsat}	collector-emitter saturation resistance	I _C = 3 A; I _B = 300 mA	[2]	-	85	105	mΩ

- [1] Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.
- [2] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$



20 V, 3 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base	3 2 1	B — (
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBSS4320X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4320X	S44

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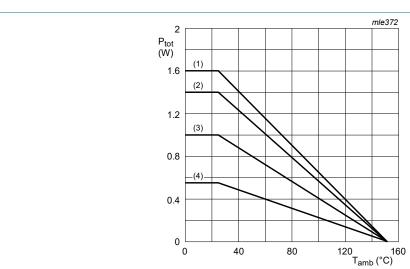
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	А
I _B	base current			-	0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	550	mW
			[3]	-	1	W
			[4]	-	1.4	W
			[5]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated.



- (1) Ceramic PCB; 7 cm² mounting pad for collector (2) FR4 PCB; 6 cm² copper mounting pad for collector (3) FR4 PCB; 1 cm² copper mounting pad for collector
- (4) Standard footprint

Power derating curves Fig. 1.

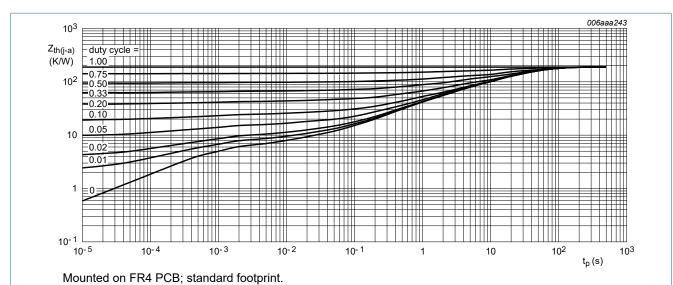
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9. Thermal characteristics

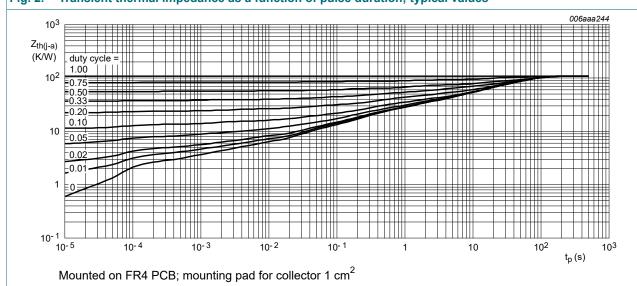
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)		unction to ambient	[1]	-	-	225	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated. [3]
- [4]

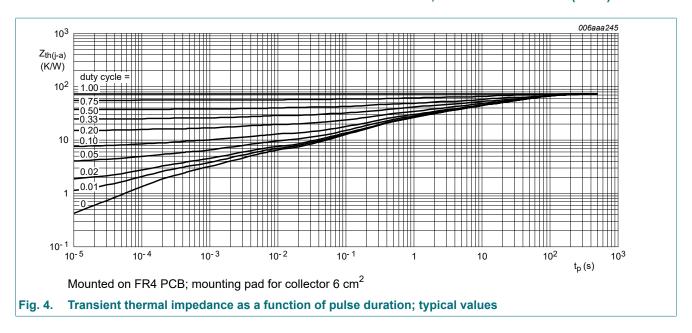


Transient thermal impedance as a function of pulse duration; typical values Fig. 2.



Transient thermal impedance as a function of pulse duration; typical values

20 V, 3 A NPN low VCEsat (BISS) transistor



10. Characteristics

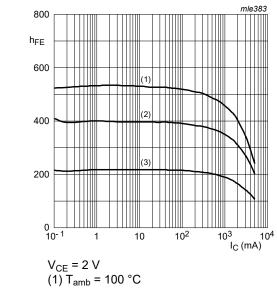
Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A		-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C		-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 20 V; V _{BE} = 0 V		-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.1 A		220	-	-	
		V _{CE} = 2 V; I _C = 0.5 A		220	-	-	
		V _{CE} = 2 V; I _C = 1 A	[1]	220	-	-	
		V _{CE} = 2 V; I _C = 2 A	[1]	200	-	-	
		V _{CE} = 2 V; I _C = 3 A	[1]	150	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 50 mA		-	-	70	mV
		I _C = 1 A; I _B = 50 mA		-	-	120	mV
		I _C = 2 A; I _B = 100 mA		-	-	240	mV
		I _C = 3 A; I _B = 300 mA	[1]	-	-	310	mV
R _{CEsat}	collector-emitter saturation resistance		[1]	-	85	105	mΩ
V _{BEsat}	base-emitter saturation	I _C = 2 A; I _B = 100 mA		-	-	1.1	V
	voltage	I _C = 3 A; I _B = 300 mA	[1]	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 1 A		1.1	-	-	V
f _T	transition frequency	V _{CE} = 5 V; I _C = 100 mA; f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	-	35	pF

[1] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$

20 V, 3 A NPN low VCEsat (BISS) transistor



$$V_{CE} = 2 V$$

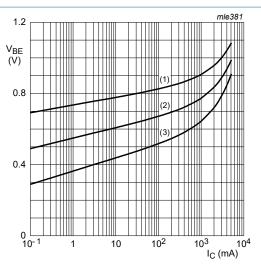
$$(1) T_{amb} = 100 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3) $T_{amb} = -55 \,^{\circ}C$

Fig. 5. DC current gain as a function of collector current; typical values



$$V_{CF} = 2 V$$

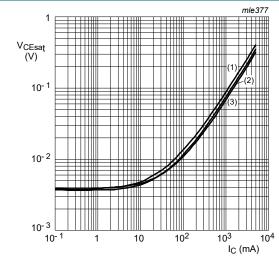
$$V_{CE} = 2 V$$

(1) $T_{amb} = -55 °C$
(2) $T_{amb} = 25 °C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



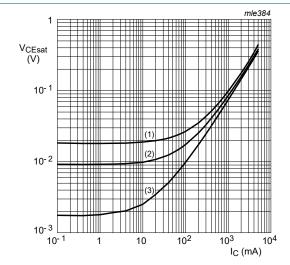
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \,^{\circ}C$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



$$I_{amb} = 25 \, ^{\circ}C$$

$$T_{amb} = 25 \, ^{\circ}C$$

(1) $I_{C}/I_{B} = 100$

(2)
$$I_{\rm C}/I_{\rm B} = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

20 V, 3 A NPN low VCEsat (BISS) transistor

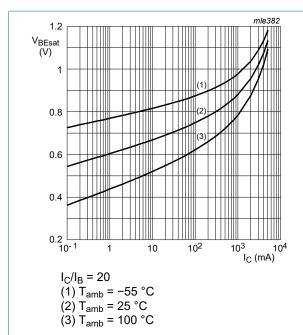
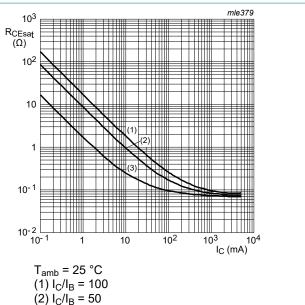
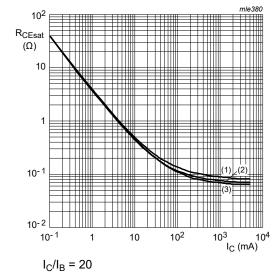


Fig. 9. collector current; typical values



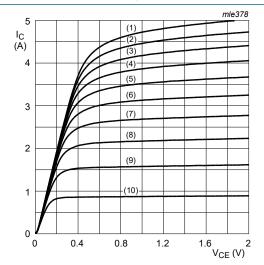
(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Base-emitter saturation voltage as a function of Fig. 10. Equivalent on-resistance as a function of collector current; typical values



(1) $T_{amb} = 100 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



T_{amb} = 25 °C (1) $I_B = 25 \text{ mA}$ (2) $I_B = 22.5 \text{ mA}$ (3) $I_B = 20 \text{ mA}$ $(4) I_B = 17.5 \text{ mA}$ $(5) I_B = 15 mA$ (6) $I_B = 12.5 \text{ mA}$

 $(7) I_B = 10 mA$

(8) $I_B = 7.5 \text{ mA}$ (9) $I_B = 5 \text{ mA}$

 $(10) I_B = 2.5 mA$

Fig. 12. Collector current as a function of collectoremitter voltage; typical values

20 V, 3 A NPN low VCEsat (BISS) transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

20 V, 3 A NPN low VCEsat (BISS) transistor

12. Package outline

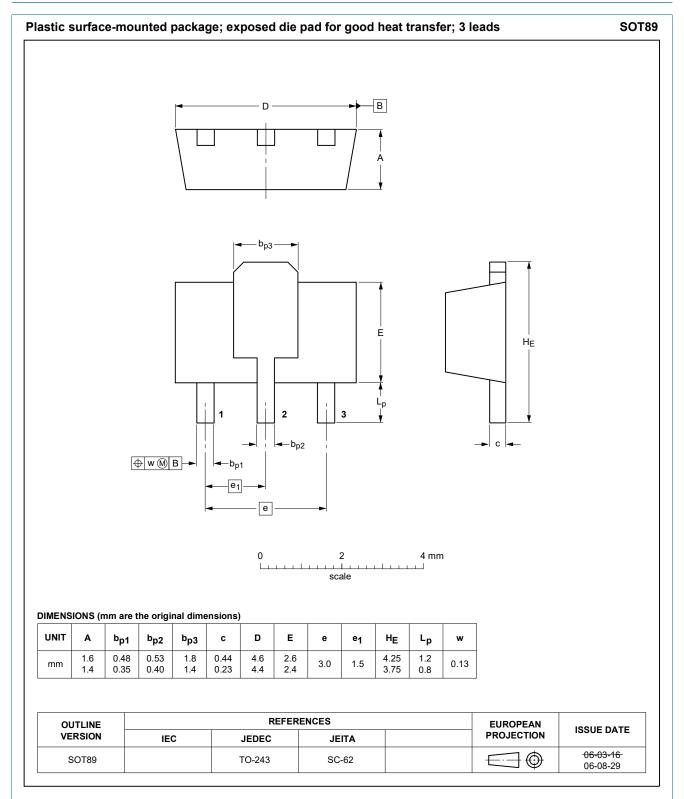
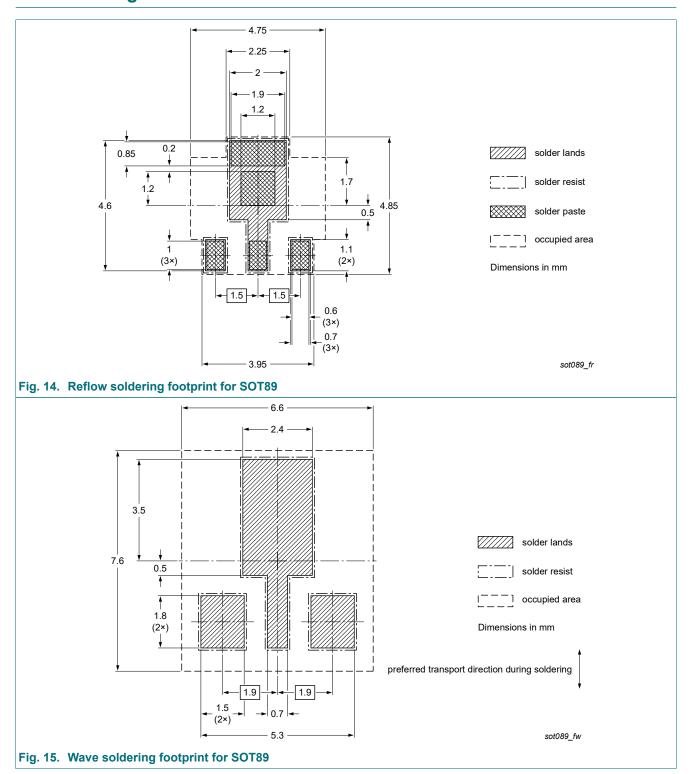


Fig. 13. Package outline SOT89

20 V, 3 A NPN low VCEsat (BISS) transistor

13. Soldering



20 V, 3 A NPN low VCEsat (BISS) transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4320X v.1	20190527	Product data sheet	-	PBSS4320X v.2
Modifications:	The format of the Nexperia.	s: V _{BEsat} corrected from typica this data sheet has been rede we been adapted to the new c	signed to comply with	
PBSS4320X v.2	20041103	Product data sheet	-	PBSS4320X v.1
PBSS4320X v.1	20031215	Product data sheet	-	-

20 V, 3 A NPN low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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20 V, 3 A NPN low VCEsat (BISS) transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10.	Characteristics	5
11.	Test information	8
12.	Package outline	9
13.	Soldering	10
14.	Revision history	.11
	Legal information	

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13 / 13

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